

L Number	Hits	Search Text	DB	Time stamp
16	1623	(si or silicon) near2 single near2 crystal\$5 near2 (substrate or wafer) near5 insulat\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/11 11:46
17	854	(si or silicon) near2 single near2 crystal\$5 near2 (substrate or wafer) near5 insulat\$5 and @py<1999	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/11 11:46
18	82	(si or silicon) near2 single near2 crystal\$5 near2 (substrate or wafer) near5 insulat\$5 and @py<1999 and 117/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/11 11:52
19	1	(tft or thin near2 film near2 transistor) same (sige or silicon near2 germanium) near4 grad\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/11 11:54
20	66	(sige or silicon near2 germanium) near4 grad\$4 same insulat\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/11 11:54
21	11	(sige or silicon near2 germanium) near4 grad\$4 near10 insulat\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/11 11:56
22	151	(sige or silicon near2 germanium) near4 grad\$4 same relax\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/11 11:56
23	29	(sige or silicon near2 germanium) near4 grad\$4 same electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/11 11:58
24	604	(sige or silicon near2 germanium) near16 ion near2 implant\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/11 11:58
25	65	(sige or silicon near2 germanium) near16 ion near2 implant\$5 near10 concentrat\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/11 12:40
26	41	(sige or silicon near2 germanium) near16 ion near2 implant\$5 near5 (ge or germanium) near10 concentrat\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/11 12:52
27	345	heterojunction near2 bipolar near2 transistor same (silicon or si) near2 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/11 12:53
28	92	heterojunction near2 bipolar near2 transistor same (silicon or si) near2 substrate same (sige or silicon near2 germanium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/11 12:53
29	5	heterojunction near2 bipolar near2 transistor same (silicon or si) near2 substrate near5 insulat\$5 same (sige or silicon near2 germanium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/11 12:55

30	0	heterojunction near2 bipolar near2 transistor same (quartz) near2 substrate same (sige or silicon near2 germanium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/11 12:55
31	0	heterojunction near2 bipolar near2 transistor same (quartz) near2 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/11 12:55
32	216	heterojunction near2 bipolar near2 transistor same insulat\$4 near2 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/11 12:58
33	520	(thin near2 film near2 transistor or tft) same (sige or silicon near2 germanium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/11 12:59
34	25	(thin near2 film near2 transistor or tft) same (sige or silicon near2 germanium) near10 (anneal\$4 or heat near2 treat\$4 or laser)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/11 13:02
35	1	(thin near2 film near2 transistor or tft) same (sige or silicon near2 germanium) near10 grad\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/11 13:00
36	11	(thin near2 film near2 transistor or tft) same (sige or silicon near2 germanium) near10 combin\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/11 13:03
37	662	amorphous near2 (silicon or si) same amorphous near5 (sige or silicon adj germanium) same (crystal\$5 or crystalliz\$4 or recrystal\$4 or recrystalliz\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/11 13:04
38	72	amorphous near2 (silicon or si) same amorphous near5 (sige or silicon adj germanium) same (crystal\$5 or crystalliz\$4 or recrystal\$4 or recrystalliz\$4) near10 (laser or heat near2 treat\$4 or anneal\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/11 13:16
39	142	(thin near2 film near2 transistor or tft) same (low near2 carrier near2 mobility)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/11 13:16
40	1	(thin near2 film near2 transistor or tft) same (low near2 carrier near2 mobility) same (sige or silicon near2 germanium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/11 13:17
41	142	(thin near2 film near2 transistor or tft) same (low near2 carrier near2 mobility)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/11 13:17
42	74	(thin near2 film near2 transistor or tft) same (low near2 carrier near2 mobility) and @py<2002	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/11 13:20
43	33	(thin near2 film near2 transistor or tft) same (carrier near2 mobility) near10 "100" and @py<2002	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/11 13:37

44	1165	polysilicon near2 insulator	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/11 13:37
45	228	polysilicon adj insulator	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/11 13:55
46	23	(silicon adj germanium or sige) near10 promot\$5 near2 (crystal\$6 or crystalliz\$4 or recrystal\$5 or recrystalliz\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/11 14:01
47	0	(silicon adj germanium or sige) near10 (si or silicon) near4 amorphous near20 (anneal\$4 or heat near2 treat\$4 or rapid near2 thermal or laser)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/11 14:02
48	58	(silicon adj germanium or sige) near10 (si or silicon) near4 amorphous near20 (anneal\$4 or heat near2 treat\$4 or rapid near2 thermal or laser)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/11 15:31
49	274	(noguchi near2 shigeru).in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/11 15:32
50	10	(noguchi near2 shigeru).in. and (sige or silicon adj germanium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/11 15:32